

三國志

Fig. 1A

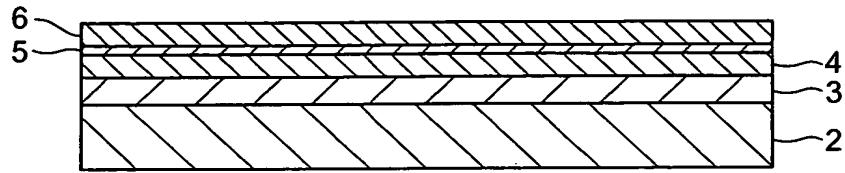


Fig. 1B

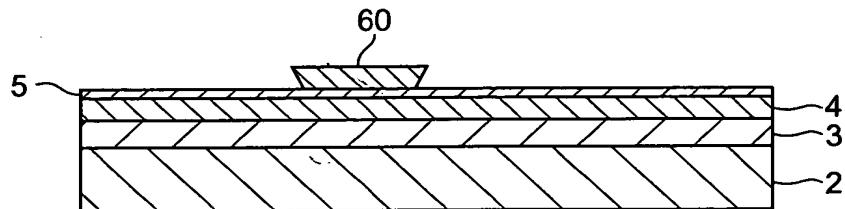


Fig. 1C

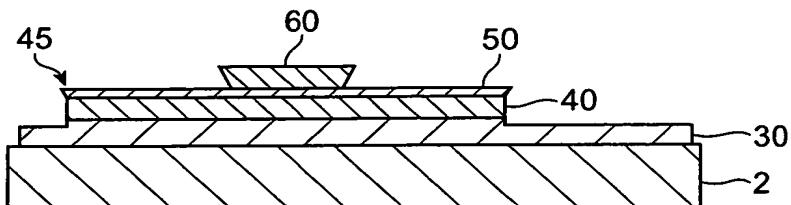


Fig. 1D

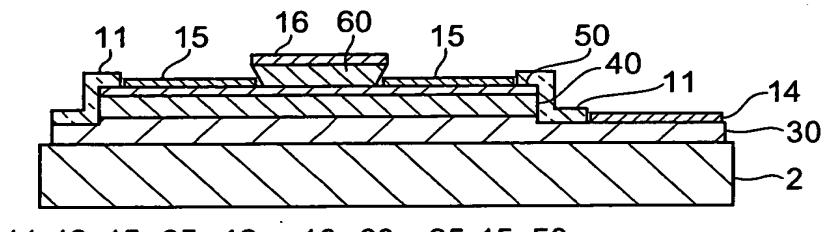


Fig. 1E

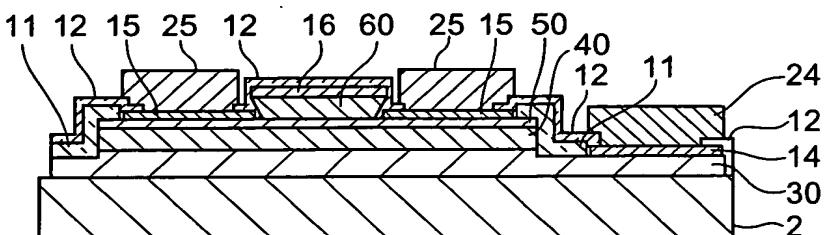


Fig. 1F

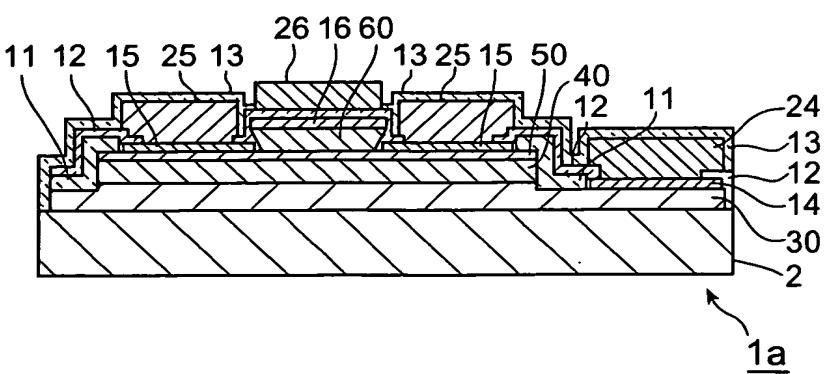
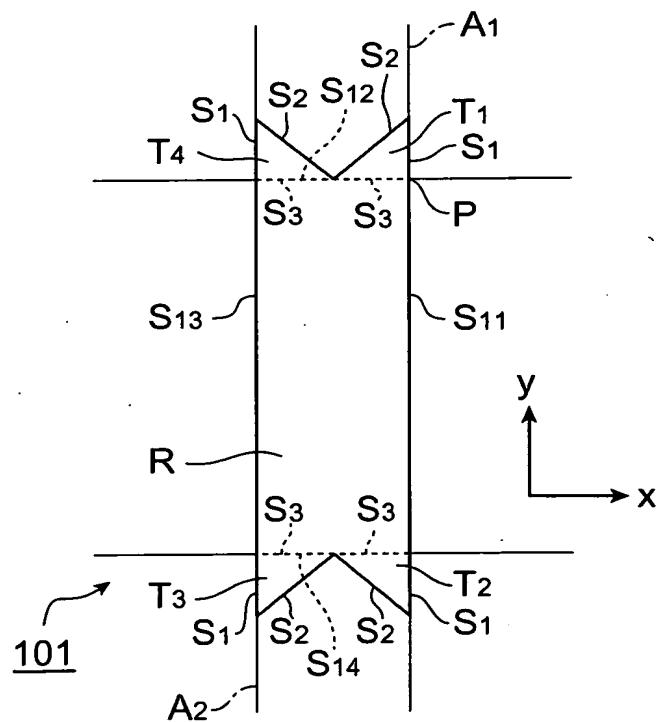


Fig.2

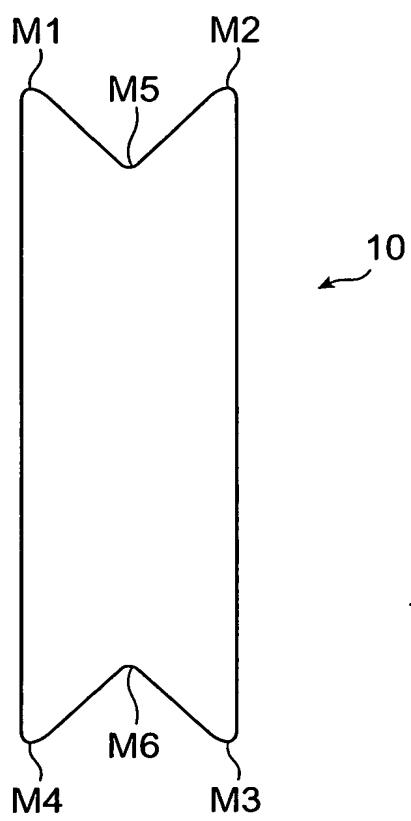
FILM NAME	MATERIALS	CONDUCTIVE TYPE	DOPANT	CARRIER CONCENTRATION (cm^{-3})	FILM THICKNESS (nm)
EMITTER FILM 6	InP	n	Si	$4\sim 20 \times 10^{18}$	250
BASE FILM 5	InGaAs	p ⁺	Zn	4×10^{19}	50
COLLECTOR FILM 4	InGaAs	n	Si	5×10^{16}	500
SUBCOLLECTOR FILM 3	InGaAs	n ⁺	Si	1×10^{19}	300

10026950-122701

Fig.3

FP01-0116-00

Fig.4



1.0026950-122701

Fig.5

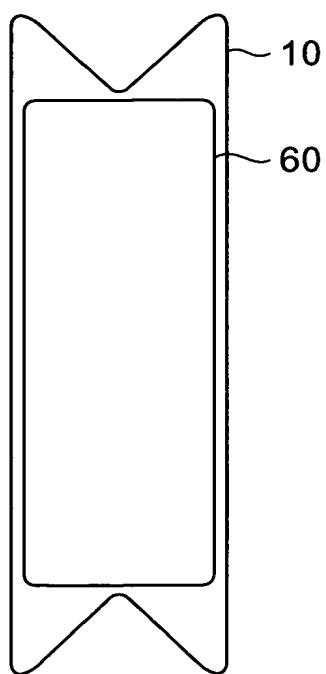


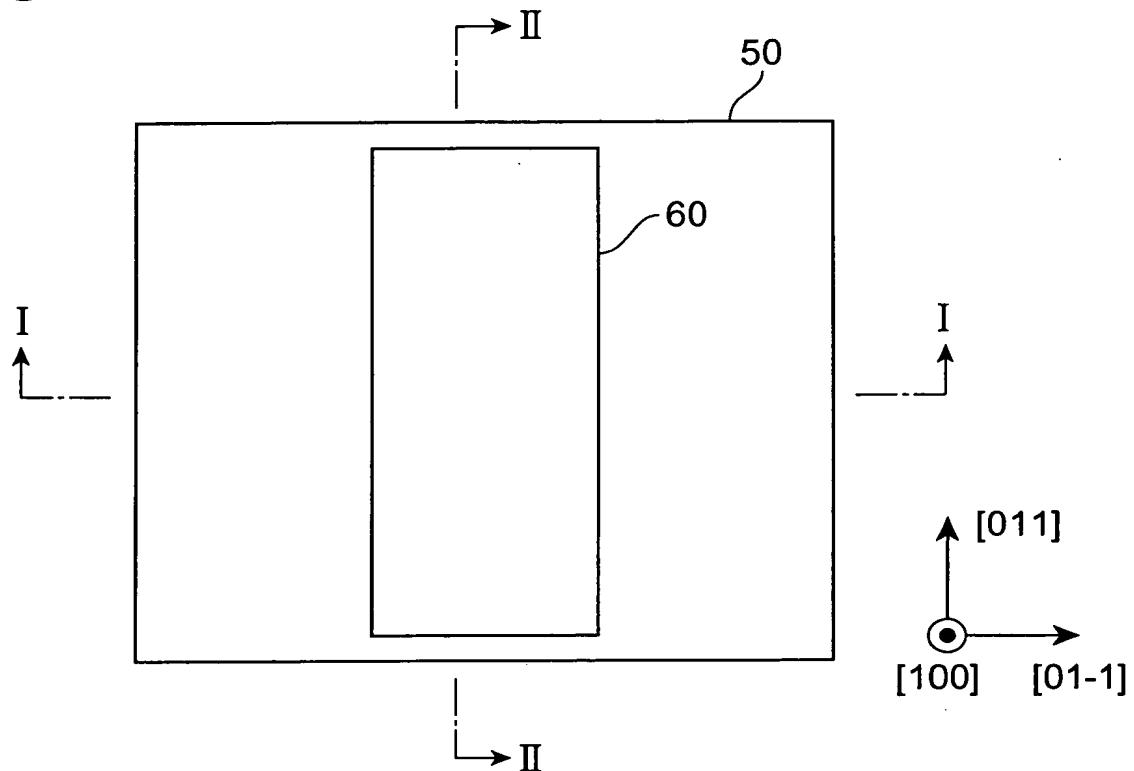
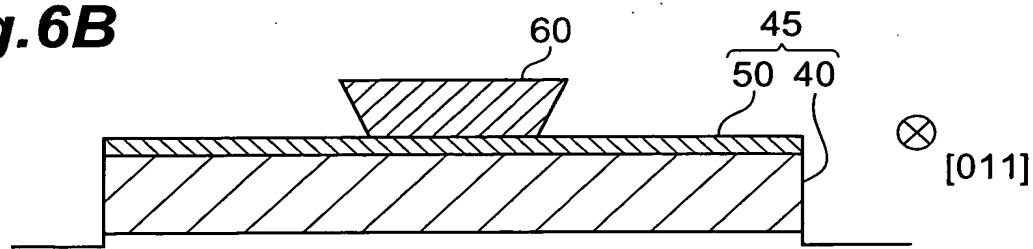
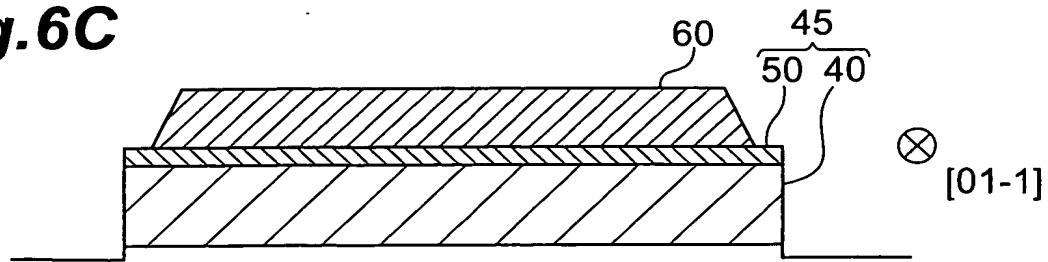
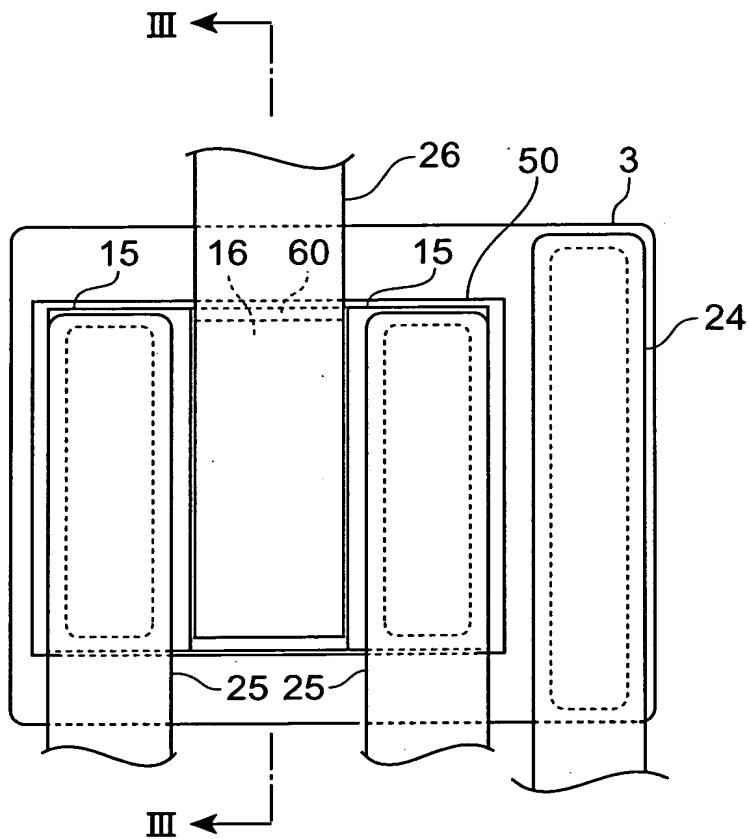
Fig. 6A**Fig. 6B****Fig. 6C**

Fig.7A

10026950-122701

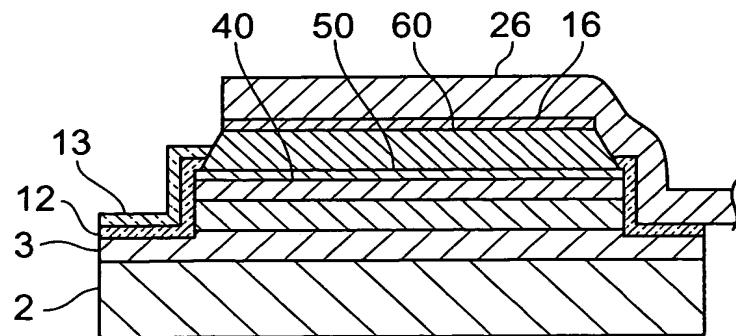
Fig.7B

FIGURE "DISG 9200"

Fig. 8A

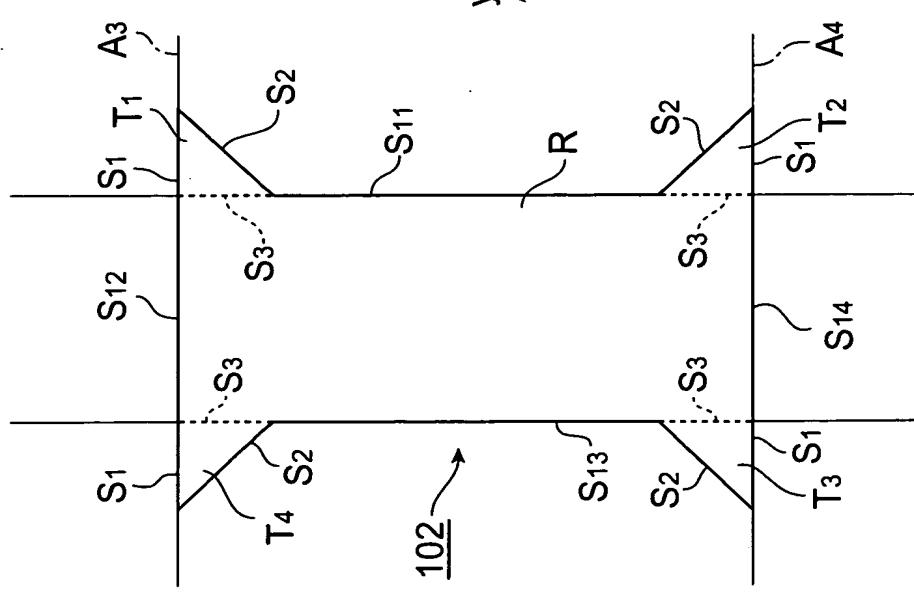
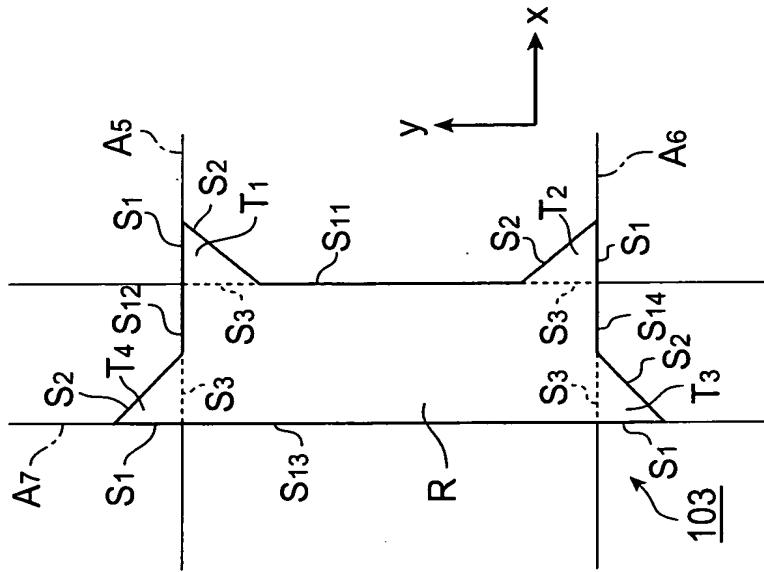


Fig. 8B



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Fig. 9A

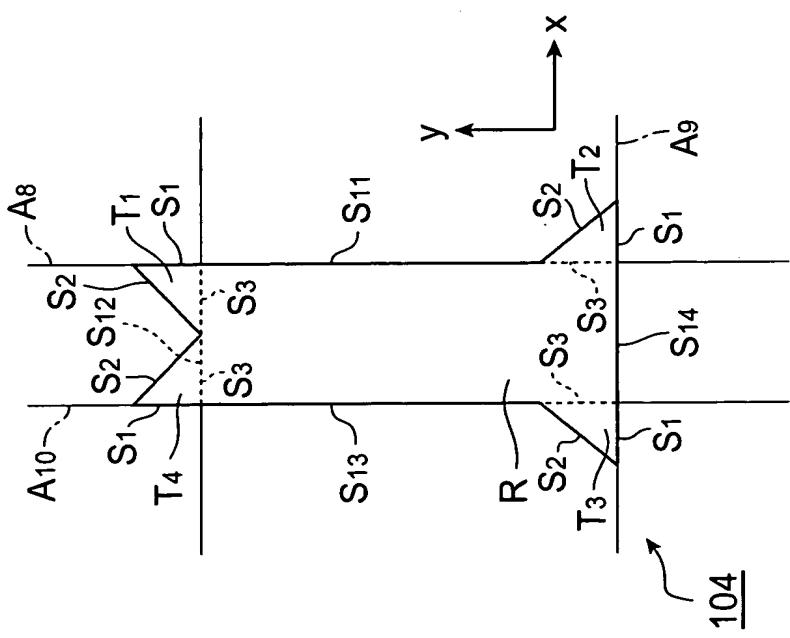


Fig. 9B

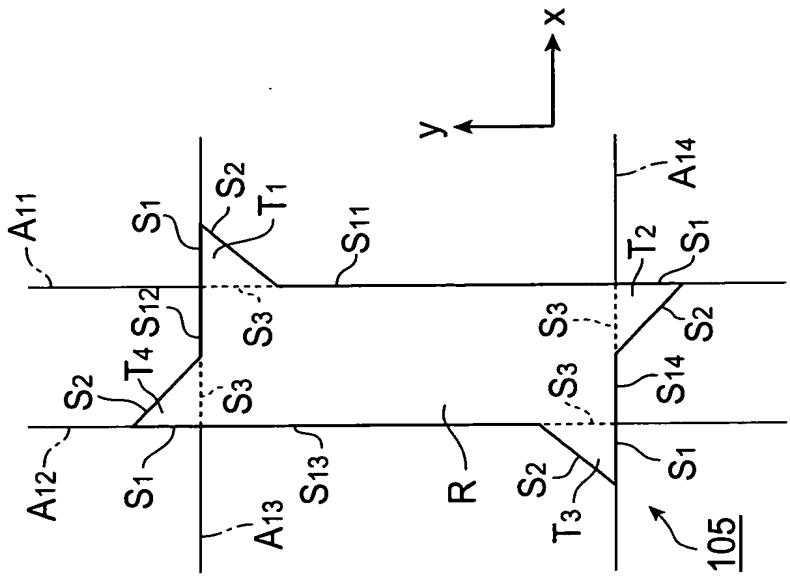


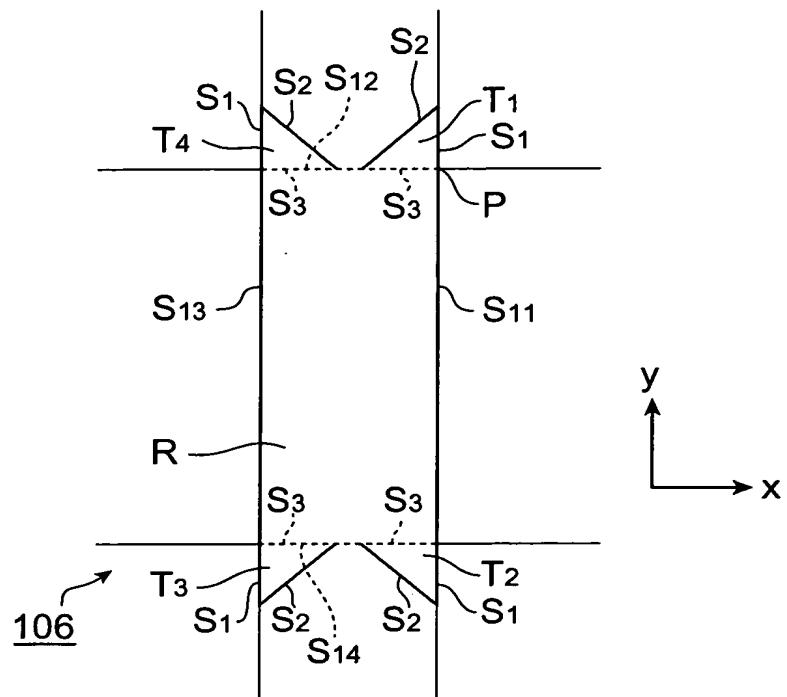
Fig.10

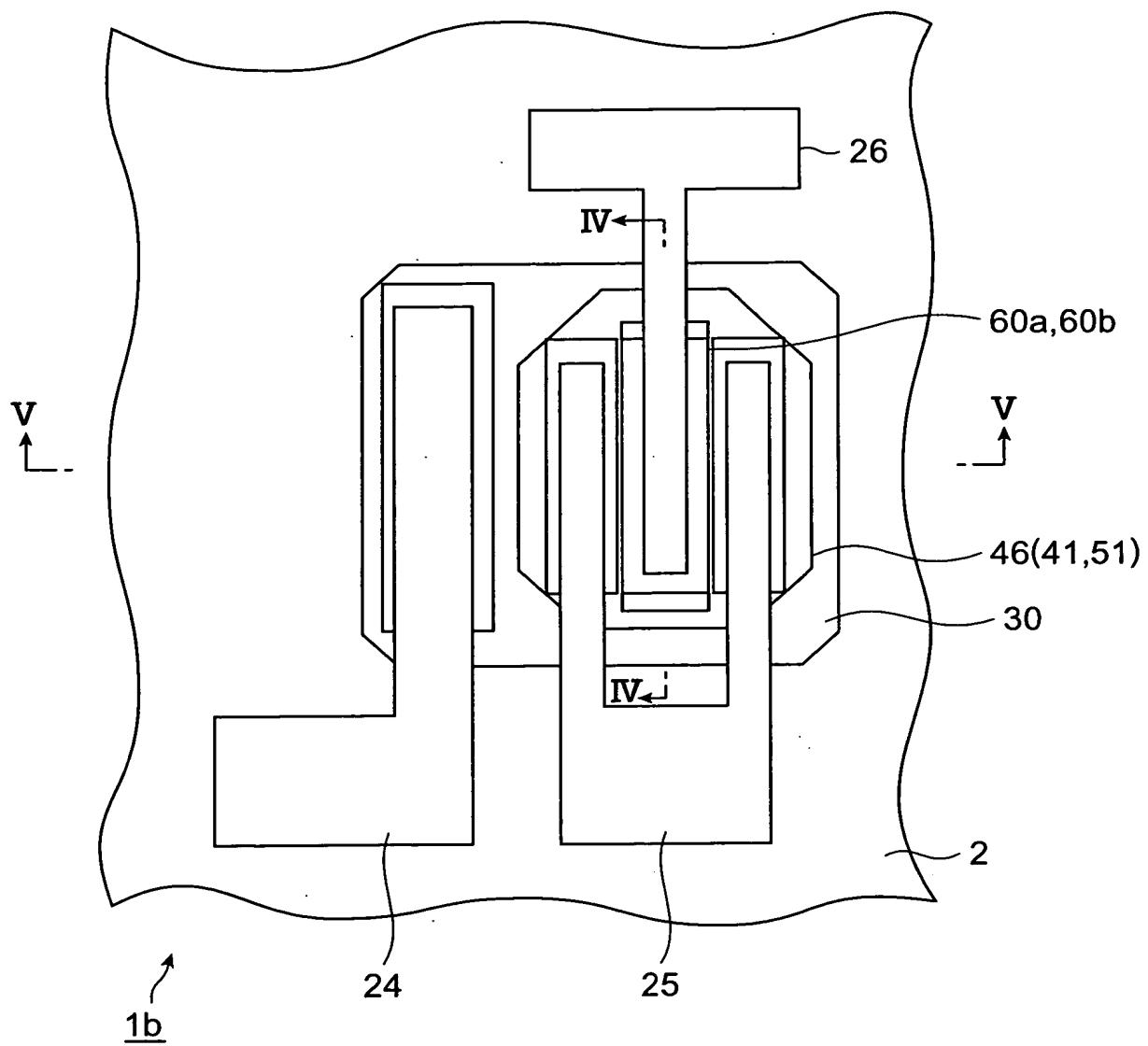
Fig.11

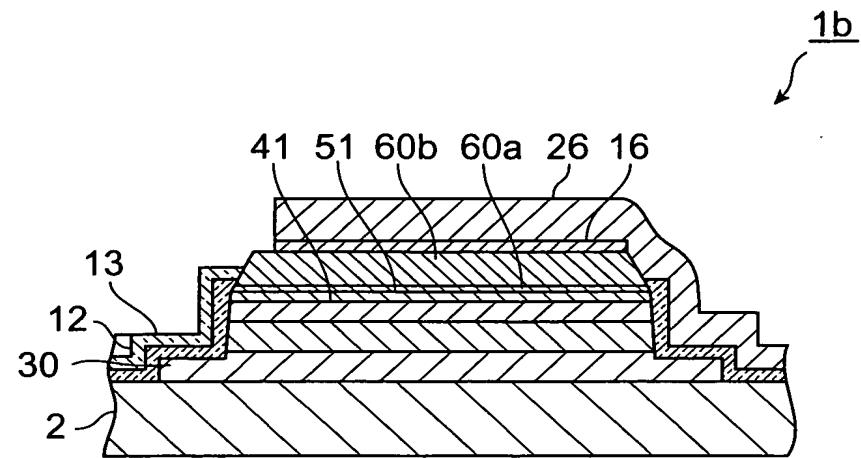
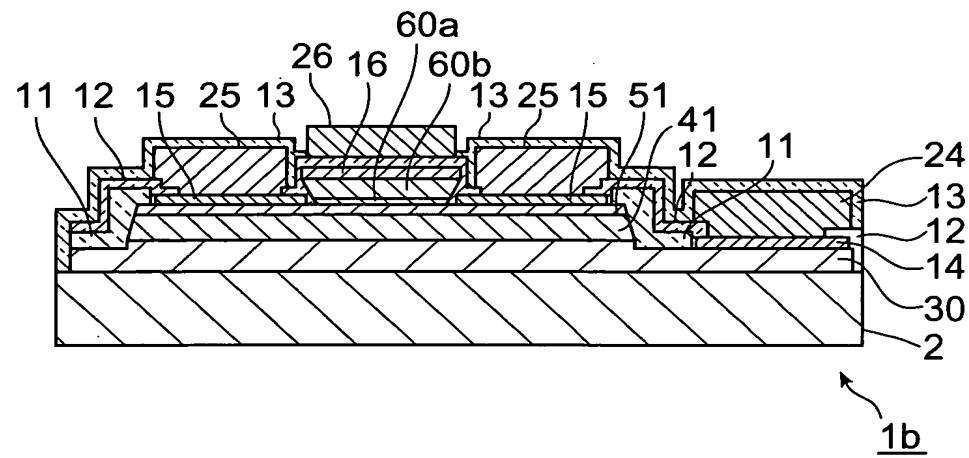
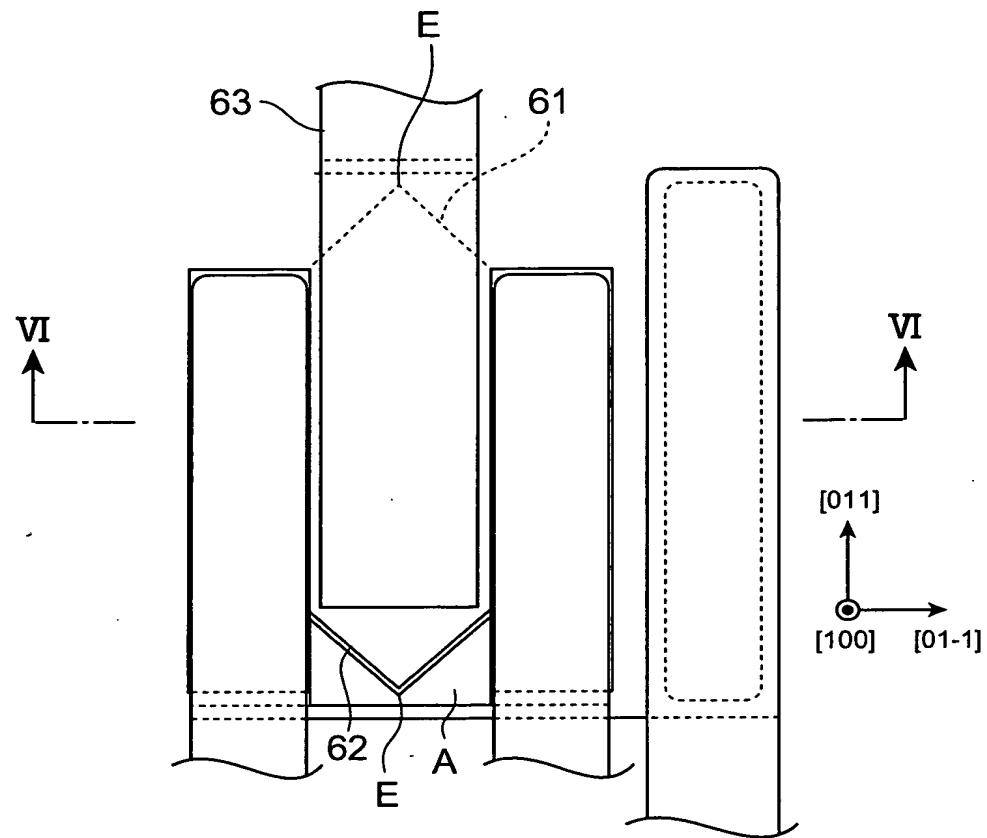
Fig.12A**Fig.12B**

Fig.13A**Fig.13B**